SQJ481EP

AUTOMOTIVE

RoHS

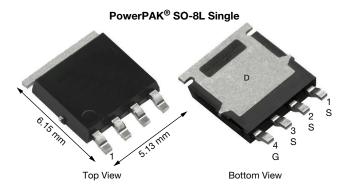
COMPLIANT HALOGEN

FREE

www.vishay.com

Vishay Siliconix

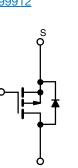
Automotive P-Channel 80 V (D-S) 175 °C MOSFET



PRODUCT SUMMARY	
V _{DS} (V)	-80
$R_{DS(on)} (\Omega)$ at $V_{GS} = -10 V$	0.0800
$R_{DS(on)} (\Omega)$ at $V_{GS} = -4.5 V$	0.0950
I _D (A)	-16
Configuration	Single
Package	PowerPAK SO-8L

FEATURES

- TrenchFET[®] power MOSFET
- AEC-Q101 qualified
- 100 % R_q and UIS tested
- Material categorization: for definitions of compliance please see <u>www.vishav.com/doc?99912</u>



P-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS (T _C	= 25 °C, unles	s otherwise noted	l)	
PARAMETER		SYMBOL	LIMIT	UNIT
Drain-source voltage		V _{DS}	-80	V
Gate-source voltage		V _{GS}	± 20	v
Continuous drain current	T _C = 25 °C	la la	-16	
	T _C = 125 °C	۱ _D	-9.2	
Continuous source current (diode conduction)		I _S	-41	A
Pulsed drain current ^a	I _{DM}	-60		
Single pulse avalanche current	L = 0.1 mH	I _{AS}	-24.5	
Single pulse avalanche energy	L = 0.1 mm	E _{AS}	30	mJ
Maximum power dissipation ^a	T _C = 25 °C	PD	45	w
	T _C = 125 °C	١D	15	vv
Operating junction and storage temperature range		T _J , T _{stg}	-55 to +175	°C
Soldering recommendations (peak temperature) c, d			260	U U

THERMAL RESISTANCE RATINGS				
PARAMETER		SYMBOL	LIMIT	UNIT
Junction-to-ambient	PCB mount ^b	R _{thJA}	70	°C/W
Junction-to-case (drain)		R _{thJC}	3.3	0/10

Notes

a. Pulse test; pulse width \leq 300 µs, duty cycle \leq 2 %

b. When mounted on 1" square PCB (FR4 material)

d. Rework conditions: manual soldering with a soldering iron is not recommended for leadless components

c. See solder profile (<u>www.vishay.com/doc?73257</u>). The PowerPAK SO-8L. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection



SPECIFICATIONS (T _C = 25 °C, unless otherwise noted)							
PARAMETER	SYMBOL	TES	T CONDITIONS	MIN.	TYP.	MAX.	UNIT
Static						1	1
Drain-Source Breakdown Voltage	V _{DS}	V _{GS} = 0, I _D = -250 μA		-80	-	-	v
Gate-Source Threshold Voltage	V _{GS(th)}		V _{GS} , I _D = -250 μA	-1.5	-2.0	-2.5	V
Gate-Source Leakage	I _{GSS}	V _{DS} =	0 V, V _{GS} = ± 20 V	-	-	± 100	nA
		$V_{GS} = 0 V$	V _{DS} = -80 V	-	-	-1	
Zero Gate Voltage Drain Current	I _{DSS}	$V_{GS} = 0 V$	V_{DS} = -80 V, T_{J} = 125 °C	-	-	-50	μA
		$V_{GS} = 0 V$	V_{DS} = -80 V, T _J = 175 °C	-	-	$\begin{array}{c c} -2.5 \\ \pm 100 & nA \\ \hline -1 & \\ -50 & \\ \mu A \\ \hline -150 & \\ 0.0800 \\ \hline 0.0140 & \\ 0.0175 \\ \hline 0.0950 & \\ \hline 0.0175 & \\ \hline 0.0950 & \\ \hline 0.0175 & \\ \hline $	
On-State Drain Current ^a	I _{D(on)}	$V_{GS} = -10 \text{ V}$	$V_{DS} = -5 V$	-10	-	-	Α
		$V_{GS} = -10 V$	I _D = -10 A	-	0.0651	0.0800	
Drain-Source On-State Resistance ^a	P	$V_{GS} = -10 V$	T _J = 125 °C	-	-	0.0140	0800 Ω 0140 Ω 0175 Ω 0950 - - S 0000 pF
Drain-Source On-State Resistance "	R _{DS(on)}	$V_{GS} = -10 V$	T _J = 175 °C	-	-	0.0175	
		V_{GS} = -4.5 V	I _D = -7 A	-	0.0775	0.0950	
Forward Transconductance b	9 _{fs}	V _{DS} = -15 V, I _D = -10 A		-	20	-	S
Dynamic ^b							
Input Capacitance	C _{iss}		V _{DS} = -25 V, f = 1 MHz	-	1459	2000	pF
Output Capacitance	C _{oss}	$V_{GS} = 0 V$		-	148	200	
Reverse Transfer Capacitance	C _{rss}			-	95	130	
Total Gate Charge ^c	Qg			-	33	50	
Gate-Source Charge ^c	Q _{gs}	V _{GS} = -10 V	$V_{DS} = -40 \text{ V}, \text{ I}_{D} = -8 \text{ A}$	-	4.5	-	nC
Gate-Drain Charge ^c	Q _{gd}			-	7.5	-	
Gate Resistance	Rg		f = 1 MHz		2.1	3.2	Ω
Turn-On Delay Time ^c	t _{d(on)}			-	12	20	
Rise Time ^c	tr	$V_{DD} = -40 \text{ V}, \text{ R}_{\text{L}} = 5 \Omega$ $\text{I}_{\text{D}} \cong -8 \text{ A}, \text{ V}_{\text{GEN}} = -10 \text{ V}, \text{ R}_{\text{g}} = 1 \Omega$		-	5	10	ns
Turn-Off Delay Time ^c	t _{d(off)}			-	32	50	
Fall Time ^c	t _f			-	6	10	
Source-Drain Diode Ratings and Chara	acteristics ^b	·					
Pulsed Current ^a	I _{SM}			-	-	-60	А
Forward Voltage	V _{SD}	$I_{\rm F} = -8 \text{ A}, V_{\rm GS} = 0$		-	-0.84	-1.2	v

Notes

a. Pulse test; pulse width \leq 300 $\mu s,$ duty cycle \leq 2 $\,\%$

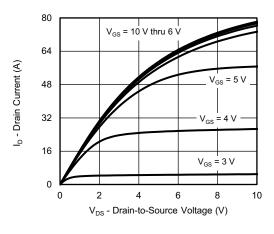
b. Guaranteed by design, not subject to production testing

c. Independent of operating temperature

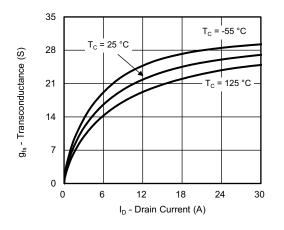
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



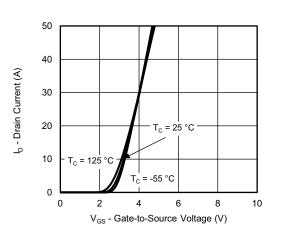
TYPICAL CHARACTERISTICS ($T_A = 25 \text{ °C}$, unless otherwise noted)



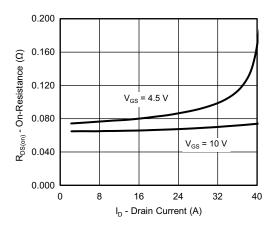
Output Characteristics



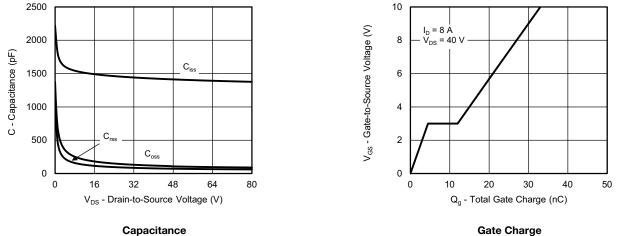
Transconductance



Transfer Characteristics



On-Resistance vs. Drain Current



Capacitance

S18-0025-Rev. A, 15-Jan-18

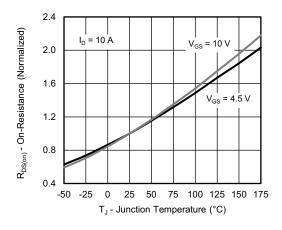
3

Document Number: 76041

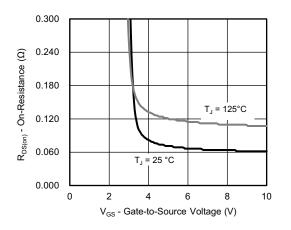
For technical questions, contact: automostechsupport@vis .com THIS DOCUMENT IS SUBJECT TO CHANGE WITHOUT NOTICE. THE PRODUCTS DESCRIBED HEREIN AND THIS DOCUMENT ARE SUBJECT TO SPECIFIC DISCLAIMERS, SET FORTH AT www.vishay.com/doc?91000



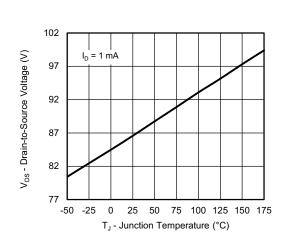
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)

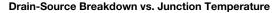


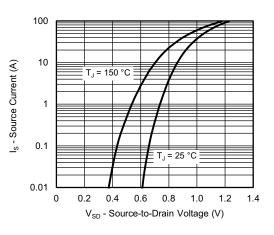
On-Resistance vs. Junction Temperature



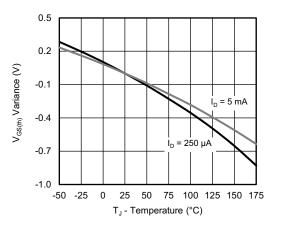
On-Resistance vs. Gate-to-Source Voltage



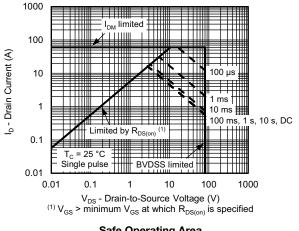




Source Drain Diode Forward Voltage



Threshold Voltage



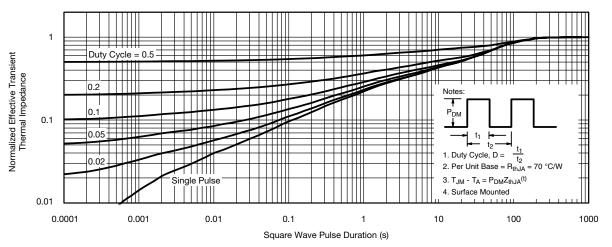
Safe Operating Area

4

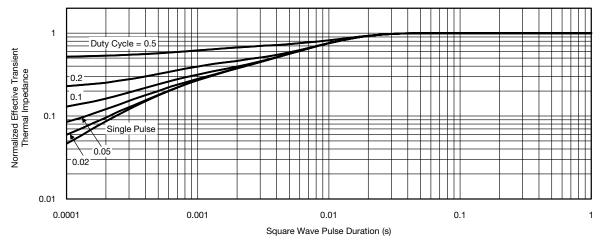
For technical questions, contact: automostech port@vishay.com THIS DOCUMENT IS SUBJECT TO CHANGE WITHOUT NOTICE. THE PRODUCTS DESCRIBED HEREIN AND THIS DOCUMENT ARE SUBJECT TO SPECIFIC DISCLAIMERS, SET FORTH AT www.vishay.com/doc?91000



THERMAL RATINGS (T_C = 25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Case

Note

- The characteristics shown in the two graphs
- Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)
- Normalized Transient Thermal Impedance Junction-to-Case (25 °C)

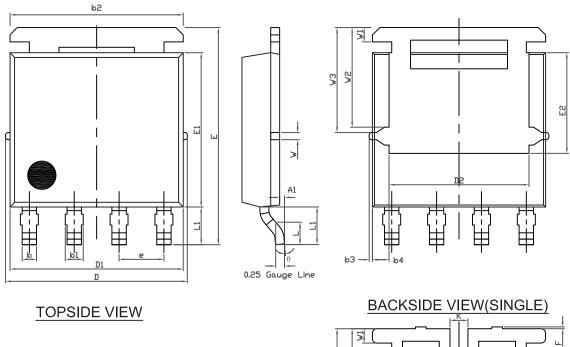
are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions

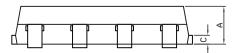
Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg?76041.

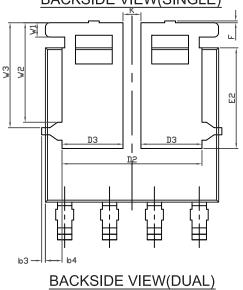
S18-0025-Rev. A, 15-Jan-18	5	Document Number: 76041
For	r technical questions, contact: <u>automostechsupport@vishay.com</u>	<u>n</u>
	O CHANGE WITHOUT NOTICE. THE PRODUCTS DESCRIBED F T TO SPECIFIC DISCLAIMERS, SET FORTH AT <u>www.vishav.com</u>	



PowerPAK[®] SO-8L Case Outline 2







Package Information



Vishay Siliconix

DIM		MILLIMETERS			INCHES			
DIM.	MIN.	NOM.	MAX.	MIN. NOM.				
А	1.00	1.07	1.14	0.039	0.042	0.045		
A1	0.00	-	0.127	0.00	-	0.005		
b	0.33	0.41	0.48	0.013	0.016	0.019		
b1	0.44	0.51	0.58	0.017	0.020	0.023		
b2	4.80	4.90	5.00	0.189	0.193	0.197		
b3		0.094	•		0.004			
b4		0.47			0.019			
С	0.20	0.25	0.30	0.008	0.010	0.012		
D	5.00	5.13	5.25	0.197	0.202	0.207		
D1	4.80	4.90	5.00	0.189	0.193	0.197		
D2	3.86	3.96	4.06	0.152	0.156	0.160		
D3	1.63	1.73	1.83	0.064	0.068	0.072		
е		1.27 BSC	•	0.050 BSC				
E	6.05	6.15	6.25	0.238	0.242	0.246		
E1	4.27	4.37	4.47	0.168	0.172	0.176		
E2	2.75	2.85	2.95	0.108	0.112	0.116		
F	-	-	0.15	-	-	0.006		
L	0.62	0.72	0.82	0.024	0.028	0.032		
L1	0.92	1.07	1.22	0.036	0.042	0.048		
К		0.51			0.020			
W		0.23			0.009			
W1		0.41			0.016			
W2	2.82			0.111				
W3		2.96			0.117			
q	0°	-	10°	0°	-	10°		

Note

• Millimeters will gover



RECOMMENDED MINIMUM PAD FOR PowerPAK[®] SO-8L SINGLE



Recommended Minimum Pads Dimensions in mm (inches)

Revision: 07-Feb-12



Vishay

Disclaimer

ALL PRODUCT, PRODUCT SPECIFICATIONS AND DATA ARE SUBJECT TO CHANGE WITHOUT NOTICE TO IMPROVE RELIABILITY, FUNCTION OR DESIGN OR OTHERWISE.

Vishay Intertechnology, Inc., its affiliates, agents, and employees, and all persons acting on its or their behalf (collectively, "Vishay"), disclaim any and all liability for any errors, inaccuracies or incompleteness contained in any datasheet or in any other disclosure relating to any product.

Vishay makes no warranty, representation or guarantee regarding the suitability of the products for any particular purpose or the continuing production of any product. To the maximum extent permitted by applicable law, Vishay disclaims (i) any and all liability arising out of the application or use of any product, (ii) any and all liability, including without limitation special, consequential or incidental damages, and (iii) any and all implied warranties, including warranties of fitness for particular purpose, non-infringement and merchantability.

Statements regarding the suitability of products for certain types of applications are based on Vishay's knowledge of typical requirements that are often placed on Vishay products in generic applications. Such statements are not binding statements about the suitability of products for a particular application. It is the customer's responsibility to validate that a particular product with the properties described in the product specification is suitable for use in a particular application. Parameters provided in datasheets and / or specifications may vary in different applications and performance may vary over time. All operating parameters, including typical parameters, must be validated for each customer application by the customer's technical experts. Product specifications do not expand or otherwise modify Vishay's terms and conditions of purchase, including but not limited to the warranty expressed therein.

Except as expressly indicated in writing, Vishay products are not designed for use in medical, life-saving, or life-sustaining applications or for any other application in which the failure of the Vishay product could result in personal injury or death. Customers using or selling Vishay products not expressly indicated for use in such applications do so at their own risk. Please contact authorized Vishay personnel to obtain written terms and conditions regarding products designed for such applications.

No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted by this document or by any conduct of Vishay. Product names and markings noted herein may be trademarks of their respective owners.